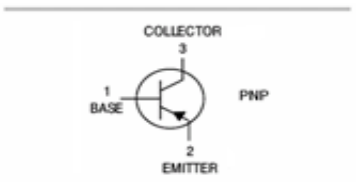
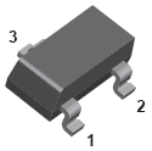
Silicon Epitaxial Planar Transistor **2SA1179**

FEATURES

HF

- High forward current transfer ratio h_{FE} which has satisfactory linearity.
- High speed switching.
- Complementary to 2SD1749.





SOT-23

APPLICATIONS

- For power application and switching.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1179	M	SOT-23

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

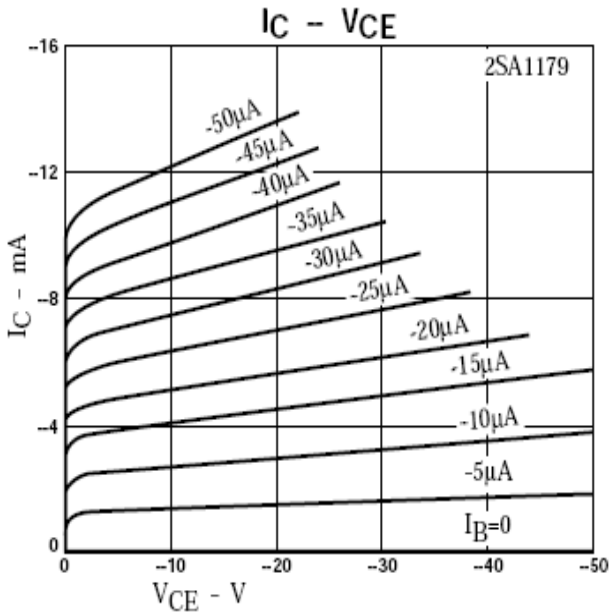
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-55	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-150	mA
P_C	Collector Dissipation	200	mW
T_J, T_{STG}	Junction and Storage Temperature	-55 to +150	℃

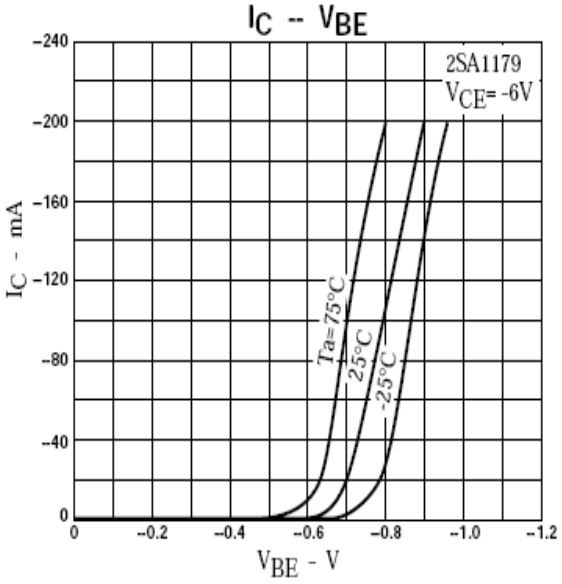
Silicon Epitaxial Planar Transistor **2SA1179**

ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

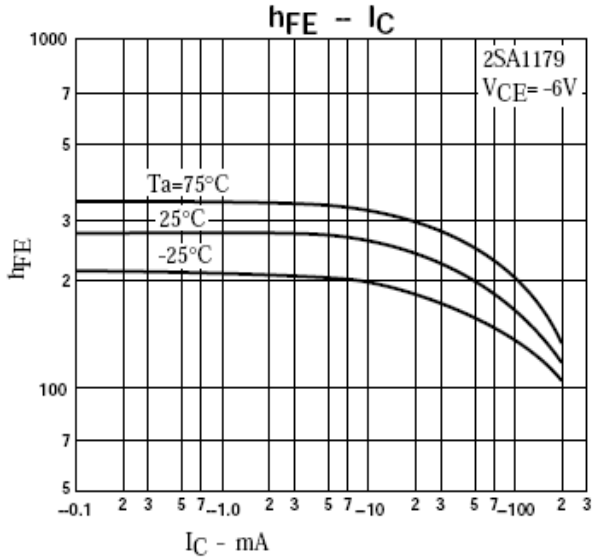
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-10μA,I_E=0	-55			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-35V,I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V,I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-6V,I_C=-1mA	200		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-50mA, I_B=-5mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-50mA, I_B=-5mA			-1.0	V
Transition frequency	f_T	V_{CE}=-6V, I_C=-10mA		180		MHz
Collector output capacitance	C_{ob}	V_{CB}=-6V,I_E=0,f=1MHz		4		pF

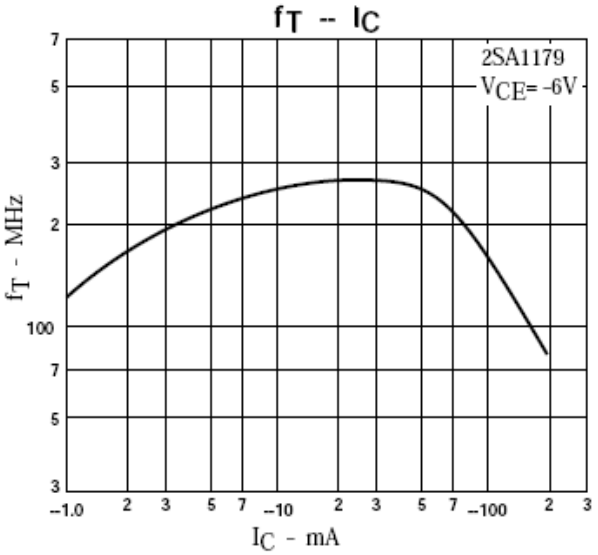
TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

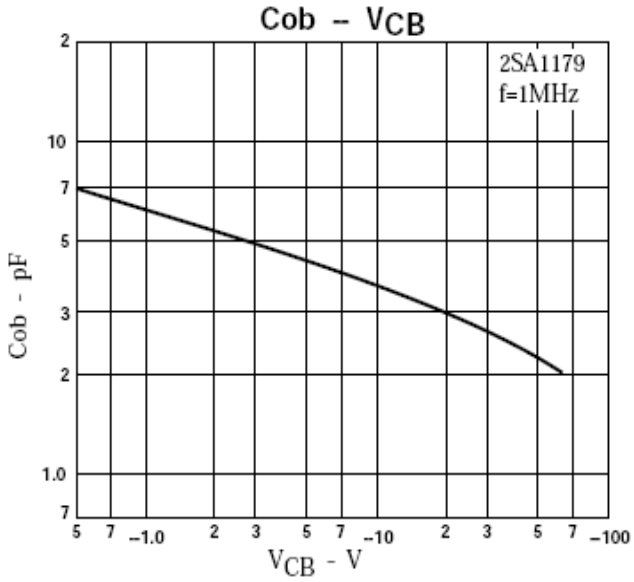


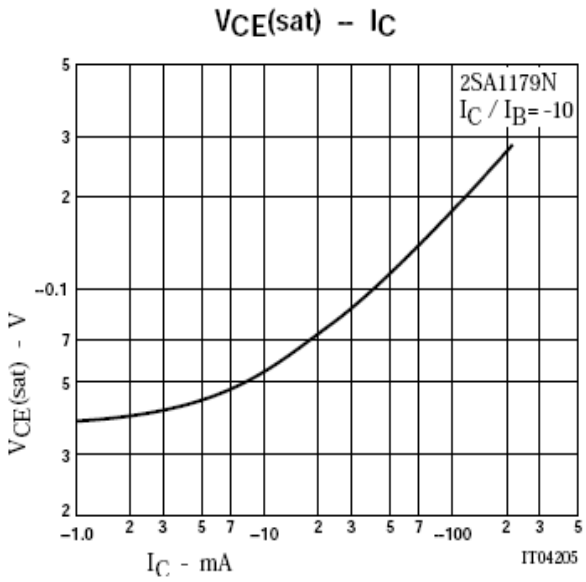


Silicon Epitaxial Planar Transistor **2SA1179**





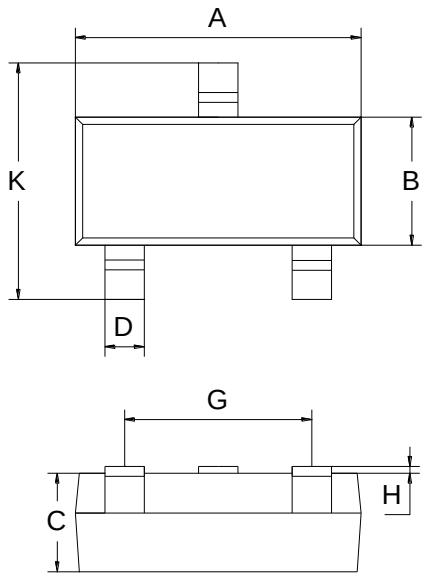




Silicon Epitaxial Planar Transistor **2SA1179**

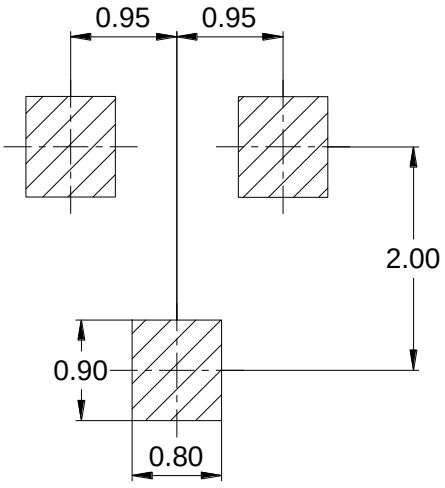
PACKAGE OUTLINE

Plastic surface mounted package SOT-23



SOT-23		
Dim	Min	Max
A	2.70	3.10
B	1.10	1.50
C	0.90	1.10
D	0.30	0.50
E	0.35	0.48
G	1.80	2.00
H	0.02	0.10
J	0.05	0.15
K	2.20	2.60
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit: mm

PACKAGE INFORMATION

Device	Package	Shipping
2SA1179	SOT-23	3000 pcs / Tape & Reel